

BLF10M6200; BLF10M6LS200

Power LDMOS transistor

Rev. 1 — 1 July 2013

Product data sheet

1. Product profile

1.1 General description

200 W LDMOS power transistor for ISM applications at frequencies from 700 MHz to 1000 MHz.

Table 1. Typical performance

Typical RF performance at $T_{case} = 25\text{ °C}$ in a common source class-AB production test circuit.

Test signal	f (MHz)	V _{DS} (V)	P _{L(AV)} (W)	G _p (dB)	η _D (%)	ACPR (dBc)
2-carrier W-CDMA	869 to 894	28	40	20	28.5	-39 ^[1]

[1] Test signal: 3GPP test model 1; 64 DPCH; PAR = 7.5 dB at 0.01 % probability on CCDF per carrier; carrier spacing 5 MHz.

1.2 Features and benefits

- Easy power control
- Integrated ESD protection
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (700 MHz to 1000 MHz)
- Internally matched for ease of use
- Compliant to Directive 2002/95/EC, regarding restriction of hazardous substances (RoHS)

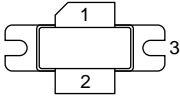
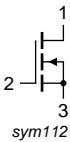
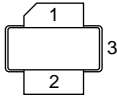
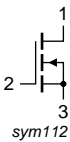
1.3 Applications

- RF power amplifiers for ISM applications in the 700 MHz to 1000 MHz frequency range.



2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
BLF10M6200 (SOT502A)			
1	drain		 sym112
2	gate		
3	source		
BLF10M6LS200 (SOT502B)			
1	drain		 sym112
2	gate		
3	source		

[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BLF10M6200	-	flanged ceramic package; 2 mounting holes; 2 leads	SOT502A
BLF10M6LS200	-	earless flanged ceramic package; 2 leads	SOT502B

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		-0.5	+13	V
T_{stg}	storage temperature		-65	+150	°C
T_j	junction temperature		[1]	225	°C

[1] Continuous use at maximum temperature will affect the reliability

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Type	Typ	Unit
$R_{th(j-case)}$	thermal resistance from junction to case	$T_{case} = 80\text{ °C};$ $P_L = 40\text{ W}$	BLF10M6200	0.50	K/W
			BLF10M6LS200	0.35	K/W

6. Characteristics

Table 6. DC characteristics

$T_j = 25\text{ }^\circ\text{C}$; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0\text{ V}$; $I_D = 0.9\text{ mA}$	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$V_{DS} = 10\text{ V}$; $I_D = 270\text{ mA}$	1.4	2.0	2.4	V
V_{GSq}	gate-source quiescent voltage	$V_{DS} = 28\text{ V}$; $I_D = 1620\text{ mA}$	1.7	2.2	2.7	V
I_{DSS}	drain leakage current	$V_{GS} = 0\text{ V}$; $V_{DS} = 28\text{ V}$	-	-	4.2	μA
I_{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75\text{ V}$; $V_{DS} = 10\text{ V}$	-	48	-	A
I_{GSS}	gate leakage current	$V_{GS} = 11\text{ V}$; $V_{DS} = 0\text{ V}$	-	-	420	nA
g_{fs}	forward transconductance	$V_{DS} = 10\text{ V}$; $I_D = 9.45\text{ A}$	-	18	-	S
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75\text{ V}$; $I_D = 9.45\text{ A}$	-	0.07	-	Ω

Table 7. AC characteristics

$T_j = 25\text{ }^\circ\text{C}$; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
C_{rs}	feedback capacitance	$V_{GS} = 0\text{ V}$; $V_{DS} = 28\text{ V}$; $f = 1\text{ MHz}$	-	3	-	pF

Table 8. RF characteristics

Test signal: 2-carrier W-CDMA; PAR 7.5 dB at 0.01 % probability on CCDF; 3GPP test model 1; 1-64 DPCH; $f_1 = 871.5\text{ MHz}$; $f_2 = 876.5\text{ MHz}$; $f_3 = 886.5\text{ MHz}$; $f_4 = 891.5\text{ MHz}$; RF performance at $V_{DS} = 28\text{ V}$; $I_{Dq} = 1400\text{ mA}$; $T_{case} = 25\text{ }^\circ\text{C}$; unless otherwise specified; in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
G_p	power gain	$P_{L(AV)} = 40\text{ W}$	19	20	-	dB
η_D	drain efficiency	$P_{L(AV)} = 40\text{ W}$	25	28.5	-	%
RL_{in}	input return loss	$P_{L(AV)} = 40\text{ W}$	-	-6.4	-4.5	dB
ACPR	adjacent channel power ratio	$P_{L(AV)} = 40\text{ W}$	-	-39.4	-36	dBc

7. Test information

7.1 Ruggedness in class-AB operation

The BLF10M6200 and BLF10M6LS200 are enhanced rugged devices and capable of withstanding a load mismatch corresponding to $VSWR = 10 : 1$ through all phases under the following conditions: $V_{DS} = 28\text{ V}$; $I_{Dq} = 1400\text{ mA}$; $P_L = 200\text{ W}$; $f = 894\text{ MHz}$

7.2 Test circuit

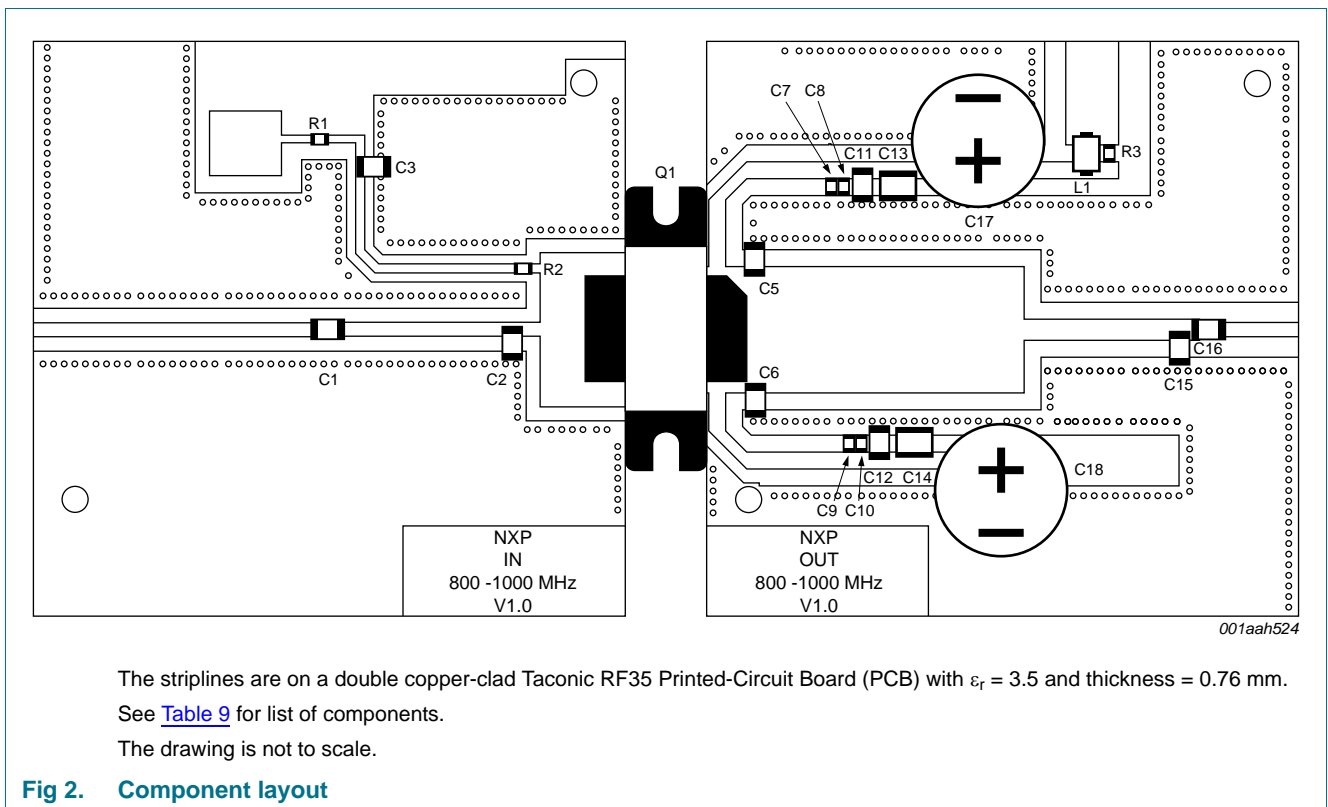
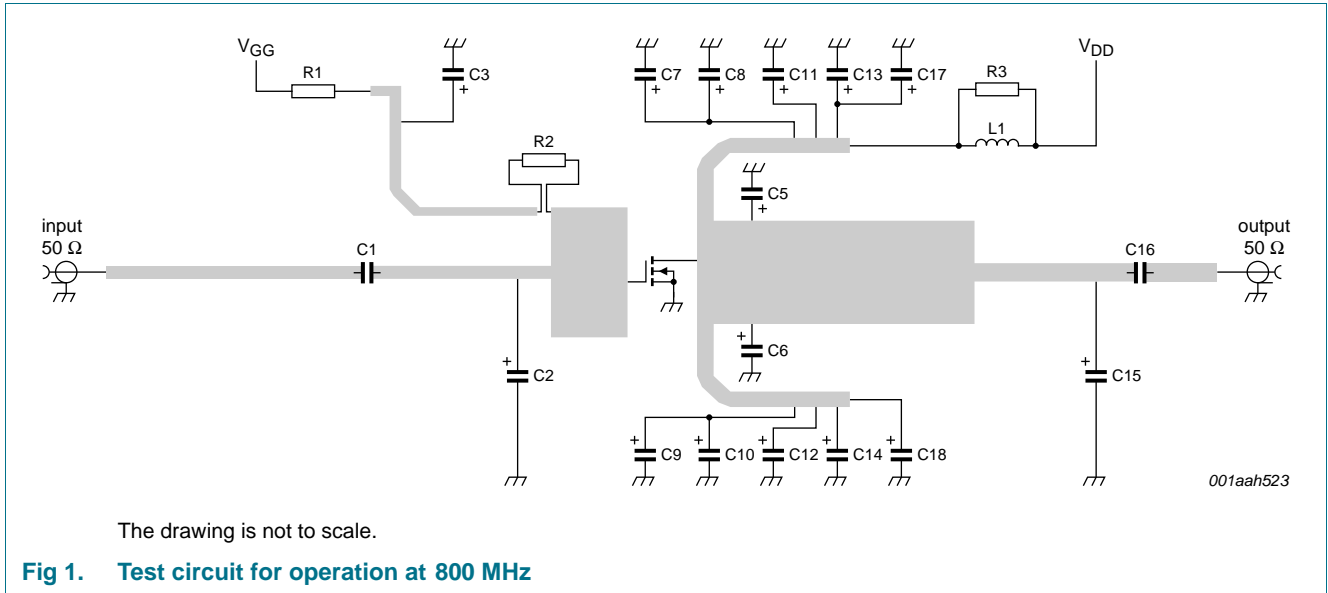


Table 9. List of components

See [Figure 1](#) and [Figure 2](#).

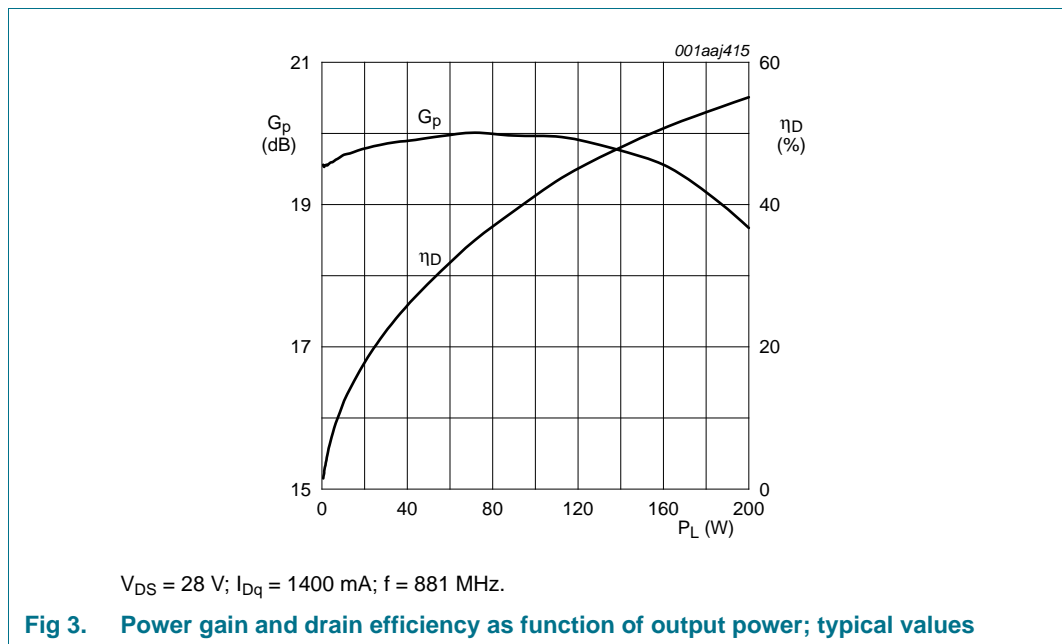
Component	Description	Value	Remarks
C1, C3, C11, C12, C16	multilayer ceramic chip capacitor	68 pF	[1] solder vertically
C2	multilayer ceramic chip capacitor	13 pF	[1] solder vertically
C5, C6	multilayer ceramic chip capacitor	10 pF	[1] solder vertically
C7, C8, C9, C10	electrolytic capacitor	220 nF	Vishay VJ1206Y224KXB
C13, C14	multilayer ceramic chip capacitor	4.7 μF, 50 V	[2]
C15	multilayer ceramic chip capacitor	1.5 pF	[1] solder vertically
C17, C18	electrolytic capacitor	220 μF, 63 V	
L1	ferrite SMD bead	-	Ferroxcube BDS 3/3/4.6-4S2 or equivalent
Q1	BLF10M6200	-	
R1, R2, R3	SMD resistor	9.1 Ω, 0.1 W	

[1] American Technical Ceramics type 100B or capacitor of same quality.

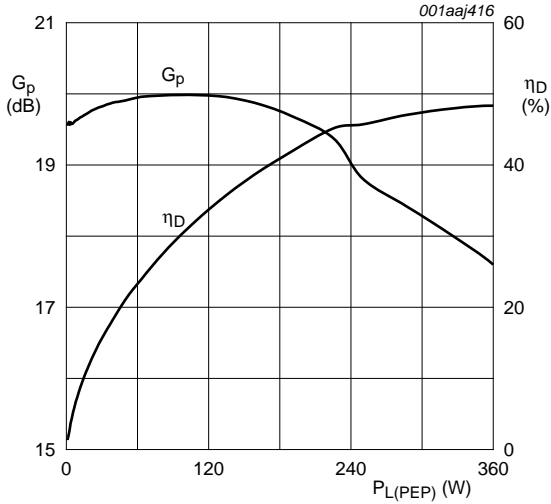
[2] TDK or capacitor of same quality.

7.3 Graphical data

7.3.1 One-tone CW

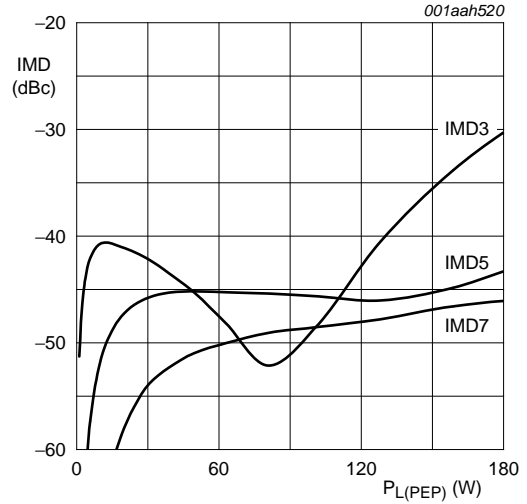


7.3.2 Two-tone CW



$V_{DS} = 28\text{ V}$; $I_{Dq} = 1400\text{ mA}$; $f = 881\text{ MHz}$ ($\pm 100\text{ kHz}$).

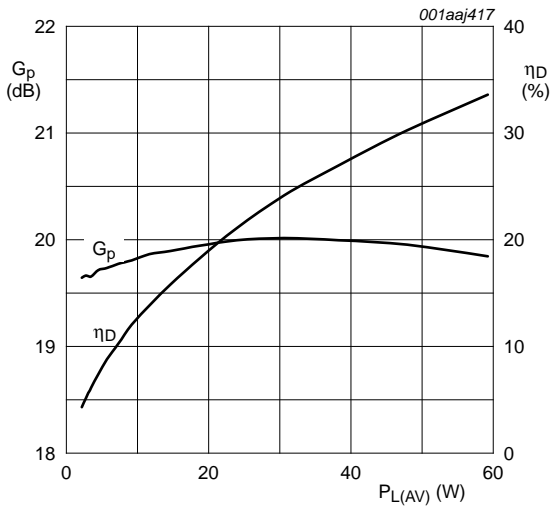
Fig 4. Power gain and drain efficiency as function of peak envelope power load power; typical values



$V_{DS} = 28\text{ V}$; $I_{Dq} = 1400\text{ mA}$; $f = 881\text{ MHz}$ ($\pm 100\text{ kHz}$).

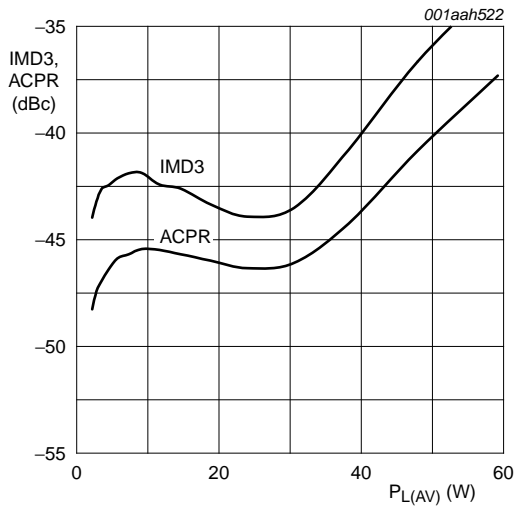
Fig 5. Intermodulation distortion as a function of peak envelope power load power; typical values

7.3.3 2-carrier W-CDMA



$V_{DS} = 28\text{ V}$; $I_{Dq} = 1400\text{ mA}$; $f = 881\text{ MHz}$ ($\pm 5\text{ MHz}$); carrier spacing 10 MHz.

Fig 6. Power gain and drain efficiency as function of average output power; typical values



$V_{DS} = 28\text{ V}$; $I_{Dq} = 1400\text{ mA}$; $f = 881\text{ MHz}$ ($\pm 5\text{ MHz}$); carrier spacing 10 MHz.

Fig 7. Adjacent channel power ratio and third order intermodulation distortion as function of average output power; typical values

8. Package outline

Flanged ceramic package; 2 mounting holes; 2 leads

SOT502A

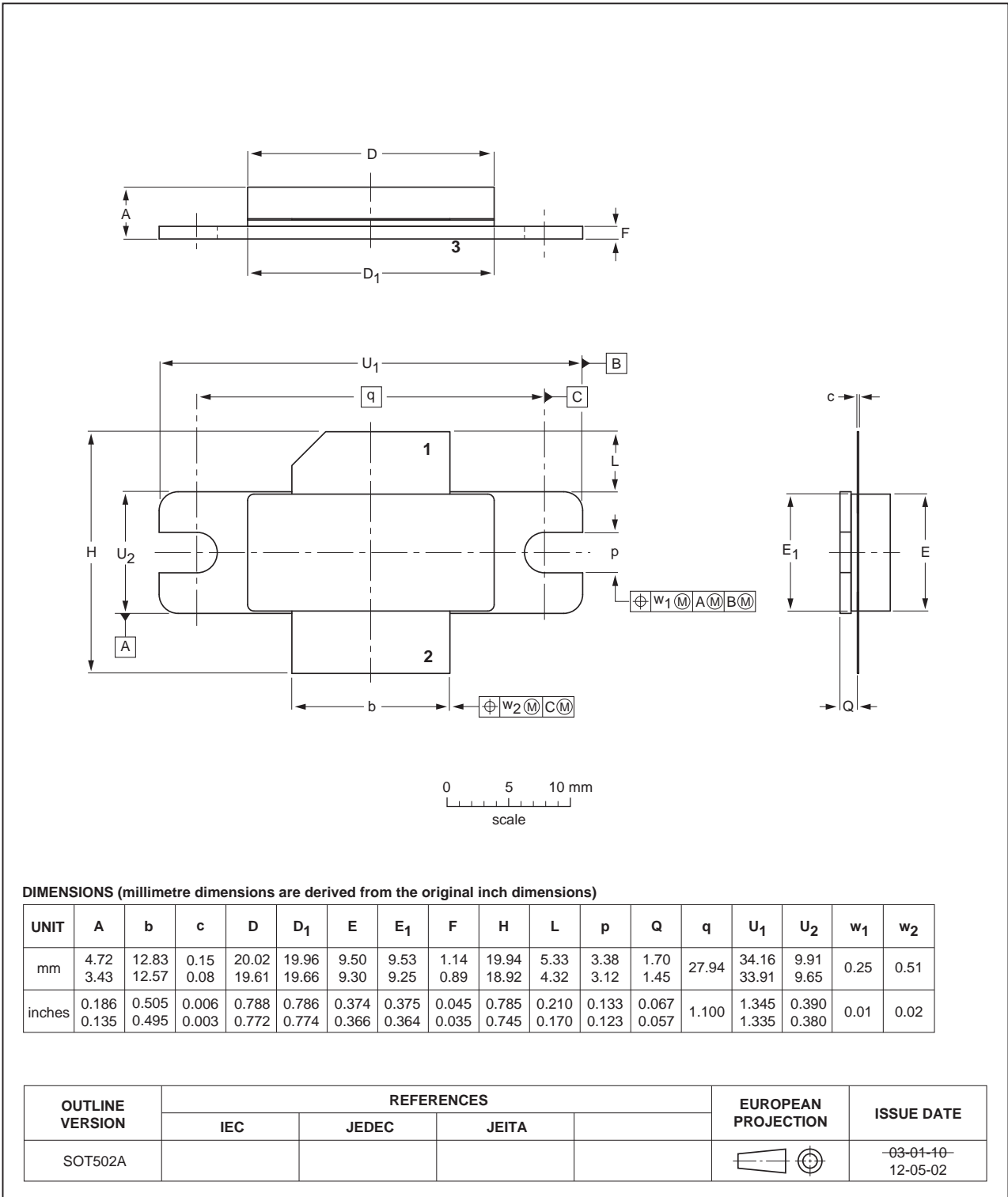


Fig 8. Package outline SOT502A

Earless flanged ceramic package; 2 leads

SOT502B

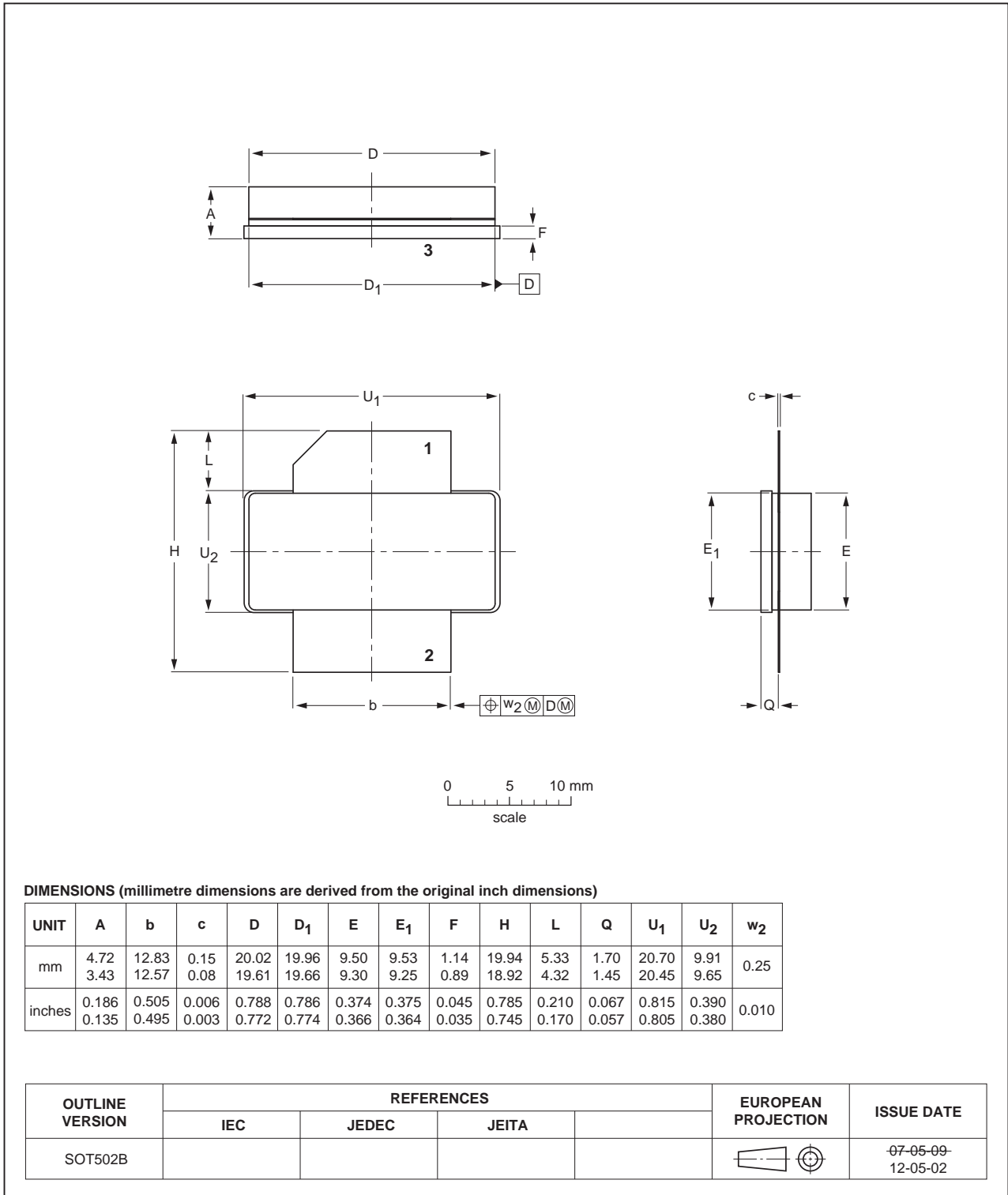


Fig 9. Package outline SOT502B

9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the *ANSI/ESD S20.20*, *IEC/ST 61340-5*, *JESD625-A* or equivalent standards.

10. Abbreviations

Table 10. Abbreviations

Acronym	Description
3GPP	3rd Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
ISM	Industrial, Scientific and Medical
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
PAR	Peak-to-Average Ratio
SMD	Surface Mounted Device
VSWR	Voltage Standing-Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

11. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF10M6200_BLF10M6LS200 v.1	20130701	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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